Honeywell Docket No. H0002800.34350 US- 4015

Buchalter Docket No.: H9945-3905

LISTING OF THE CURRENT CLAIMS IN ACCORDANCE WITH REVISED AMENDMENT PRACTICE

Claims 1-66:

Canceled.

67. (Currently Amended) A three-dimensional physical vapor deposition target, comprising:

a material comprising one or more of Cu, Ni, Co, Ta, Al, and Ti;

an average grain size of less than or equal to 250 microns within the material;

a shape, the shape including at least one cup having a first end and a second end in opposing relation to the first end; the first end having an opening extending therein; the cup having a hollow therein; the hollow extending from the opening in the first end toward the second end; the cup having an interior surface defining a periphery of the hollow; and

a sputtering surface defined along the interior surface of the cup, wherein the target is monolithic and comprises a cast ingot.

- 68. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of copper; and wherein the target consists essentially of the material.
- 69. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of tantalum; and wherein the target consists essentially of the material.
- 70. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of CuSn, with the Sn being present to from about 100 ppm, by weight, to about 3 atomic percent; and wherein the target consists essentially of the material.
- (Original) The three-dimensional physical vapor deposition target of claim 67
 wherein the material consists essentially of CuAl, with the Al being present to from

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about 100 ppm, by weight, to about 3 atomic percent; and wherein the target

consists essentially of the material.

72. (Original) The three-dimensional physical vapor deposition target of claim 67 wherein the material consists essentially of CuAg, with the Ag being present to from about 100 ppm, by weight, to about 3 atomic percent; and wherein the target

consists essentially of the material.

73. (Original) The three-dimensional physical vapor deposition target of claim 67

wherein the average grain size is less than or equal to 200 microns.

74. (Original) The three-dimensional physical vapor deposition target of claim 67

wherein the average grain size is less than or equal to 100 microns.

75. (Original) The three-dimensional physical vapor deposition target of claim 67

wherein the average grain size is less than or equal to 90 microns.

76. (Original) The three-dimensional vapor deposition target of claim 67 wherein the

average grain size is less than or equal to 85 microns.

Claims 77-89: Canceled.